



STC08IE120HV

Emitter Switched Bipolar Transistor
ESBT[®] 1200 V - 8 A - 0.10 Ω

General features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
0.8 V	8 A	0.10 Ω

- High voltage / high current Cascode configuration
- Low equivalent on resistance
- very fast-switch up to 150 kHz
- Squared RBSOA up to 1200V
- Very low C_{iss} driven by $R_G = 47\Omega$
- Very low turn-off cross over time

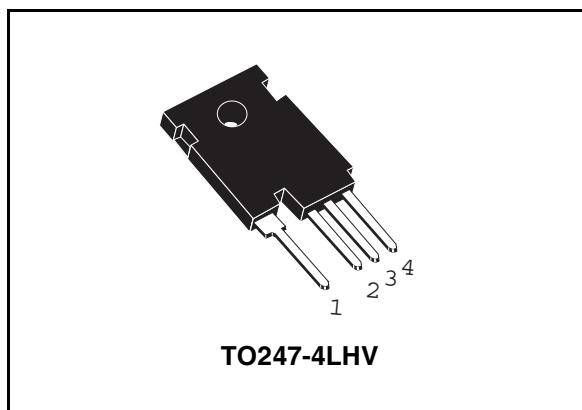
Applications

- Flyback / forward SMPS
- Buck-boost converter

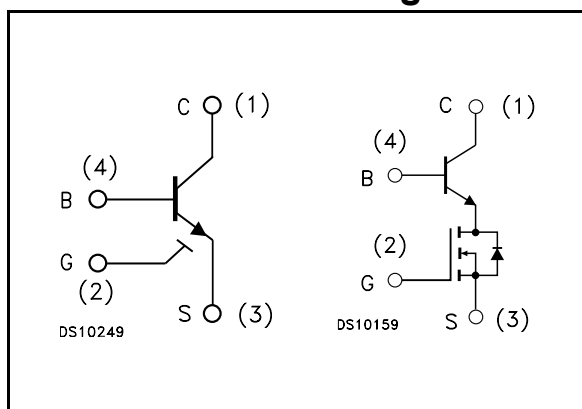
Description

The STC08IE120HV is manufactured in Monolithic ESBT Technology, aimed to provide best performances in high frequency / high voltage applications.

It is designed for use in Gate Driven based topologies.



Internal schematic diagrams



Order codes

Part Number	Marking	Package	Packing
STC08IE120HV	C08IE120HV	TO247-4LHV	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	5
2.2	Test circuits	7
3	Package mechanical data	8

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ($V_{BS} = V_{GS} = 0$ V)	1200	V
$V_{BS(OS)}$	Base-source voltage ($I_C = 0$, $V_{GS} = 0$ V)	30	V
$V_{SB(OS)}$	Source-base voltage ($I_C = 0$, $V_{GS} = 0$ V)	17	V
V_{GS}	Gate-source voltage	± 17	V
I_C	Collector current	8	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	24	A
I_B	Base current	6	A
I_{BM}	Base peak current ($t_P < 5$ ms)	12	A
P_{tot}	Total dissipation at $T_c = 25^\circ\text{C}$	208	W
T_{stg}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.6	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{\text{CS(SS)}}$	Collector-source current ($V_{\text{BS}} = V_{\text{GS}} = 0$)	$V_{\text{CE}} = 1200\text{V}$			100	μA
$I_{\text{BS(OS)}}$	Base-source current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{BS(OS)}} = 30\text{V}$			10	μA
$I_{\text{SB(OS)}}$	Source-base current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$)	$V_{\text{SB(OS)}} = 17\text{V}$			100	μA
$I_{\text{GS(OS)}}$	Gate-source leakage	$V_{\text{GS}} = \pm 17\text{V}$			100	nA
$V_{\text{CS(ON)}}$	Collector-source ON voltage	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $I_{\text{B}} = 1.6\text{A}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.4\text{A}$		0.8 0.5	1 1.2	V V
h_{FE}	DC current gain	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $V_{\text{CS}} = 1\text{V}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 4\text{A}$ $V_{\text{CS}} = 1\text{V}$	5 7			
$V_{\text{BS(ON)}}$	Base Source ON voltage	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $I_{\text{B}} = 1.6\text{A}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.4\text{A}$		1.5 1.5		V V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{BS}} = V_{\text{GS}}$ $I_{\text{B}} = 250\mu\text{A}$	2	3	4	V
C_{ISS}	Input capacitance	$V_{\text{CS}} = 25\text{V}$ $f = 1\text{MHz}$ $V_{\text{GS}} = 0$		550		pF
$Q_{\text{GS(tot)}}$	Gate-source charge	$V_{\text{GS}} = 10\text{V}$		26		nC
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.8\text{A}$ $V_{\text{GS}} = 10\text{V}$ $V_{\text{Clamp}} = 960\text{V}$ $R_{\text{G}} = 47\Omega$ $t_{\text{p}} = 4\mu\text{s}$		670 15		ns ns
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.4\text{A}$ $V_{\text{GS}} = 10\text{V}$ $V_{\text{Clamp}} = 960\text{V}$ $R_{\text{G}} = 47\Omega$ $t_{\text{p}} = 4\mu\text{s}$		340 10.2		ns ns
V_{CSW}	Maximum collector-source voltage switched without snubber	$R_{\text{G}} = 47\Omega$ $h_{\text{FE}} = 5\text{A}$ $I_{\text{C}} = 8\text{A}$	1200			V
$V_{\text{CS(dyn)}}$	Collector-source dynamic voltage (500ns)	$V_{\text{CC}} = V_{\text{Clamp}} = 400\text{V}$ $V_{\text{GS}} = 10\text{V}$ $R_{\text{G}} = 47\Omega$ $I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.8\text{A}$ $I_{\text{Bpeak}} = 4\text{A}$ $t_{\text{peak}} = 500\text{ns}$		5.75		V
$V_{\text{CS(dyn)}}$	Collector-source dynamic voltage (1 μs)	$V_{\text{CC}} = V_{\text{Clamp}} = 400\text{V}$ $V_{\text{GS}} = 10\text{V}$ $R_{\text{G}} = 47\Omega$ $I_{\text{C}} = 4\text{A}$ $I_{\text{B}} = 0.8\text{A}$ $I_{\text{Bpeak}} = 4\text{A}$ $t_{\text{peak}} = 500\text{ns}$		3.35		V

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

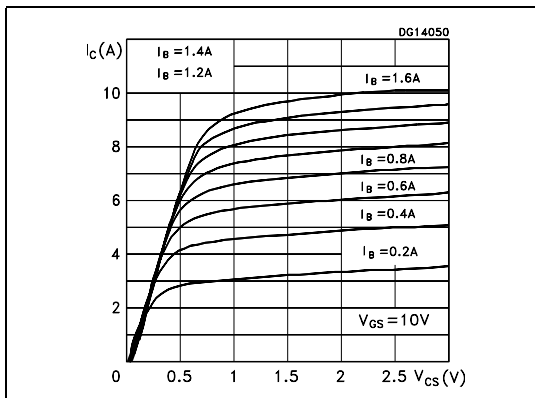


Figure 2. DC current gain

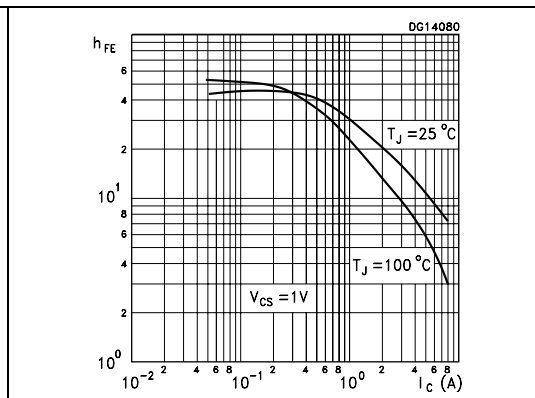


Figure 3. Collector-source On voltage

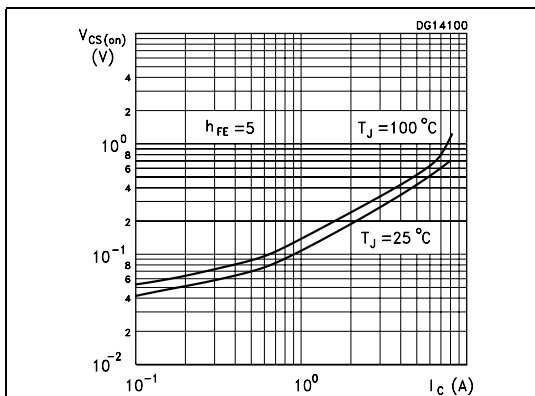


Figure 4. Collector-source On voltage

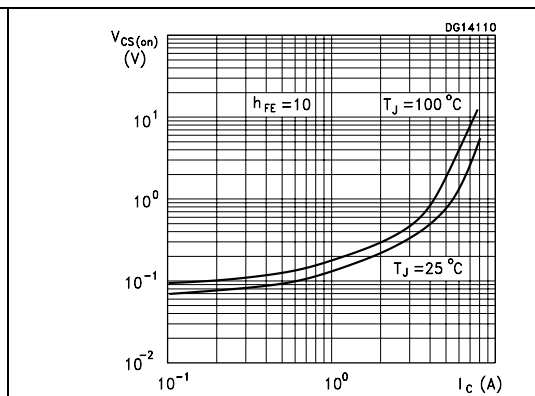


Figure 5. Base-source On voltage

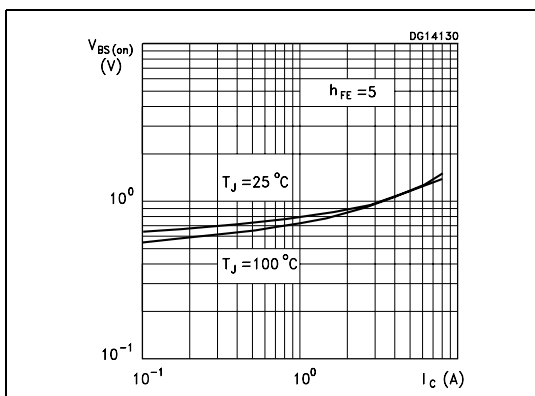


Figure 6. Base-source On voltage

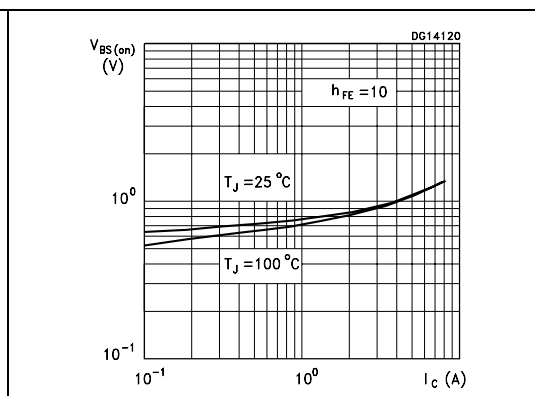


Figure 7. Reverse biased safe operating area

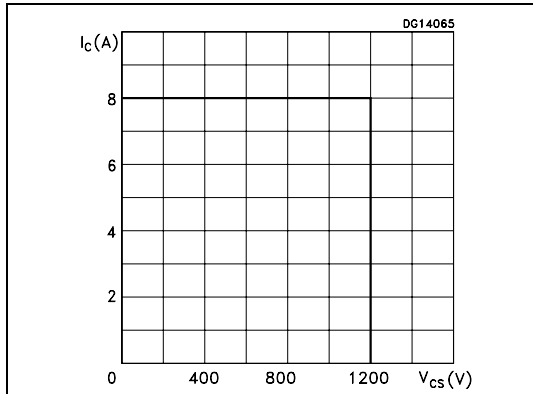


Figure 8. Gate threshold voltage vs temperature

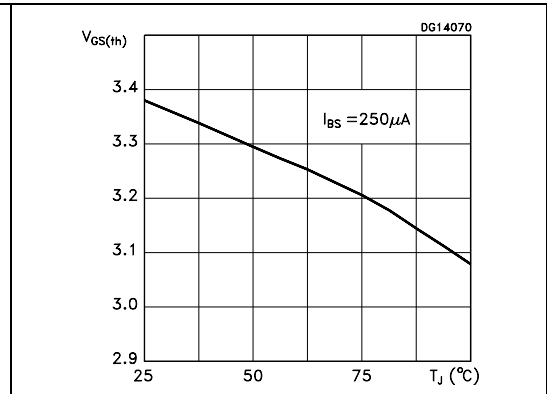


Figure 9. Dynamic collector-emitter saturation voltage

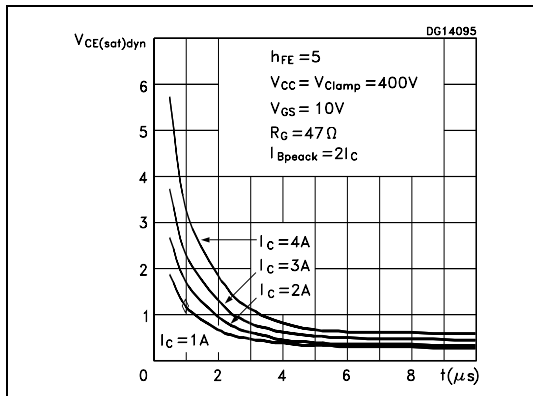


Figure 10. Inductive load switching time

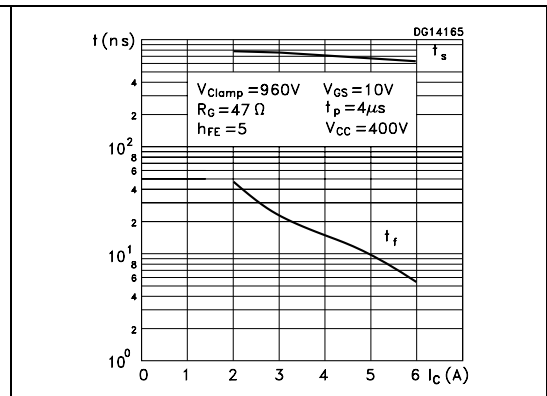
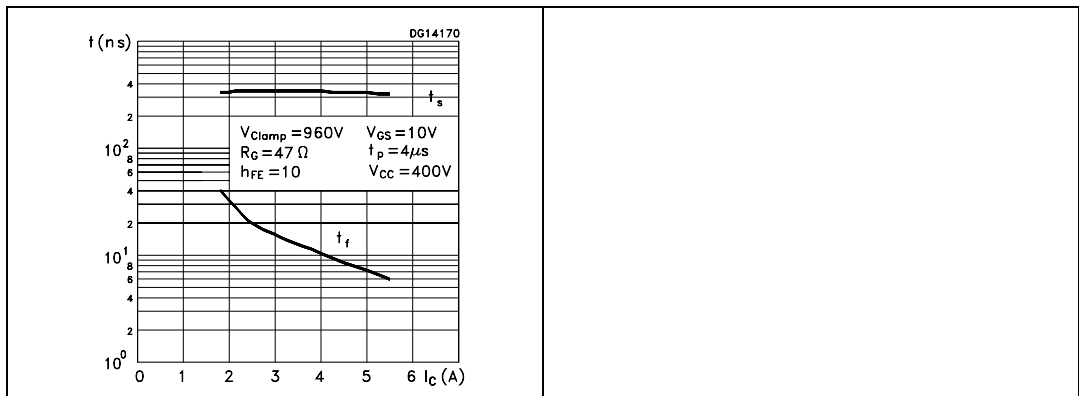
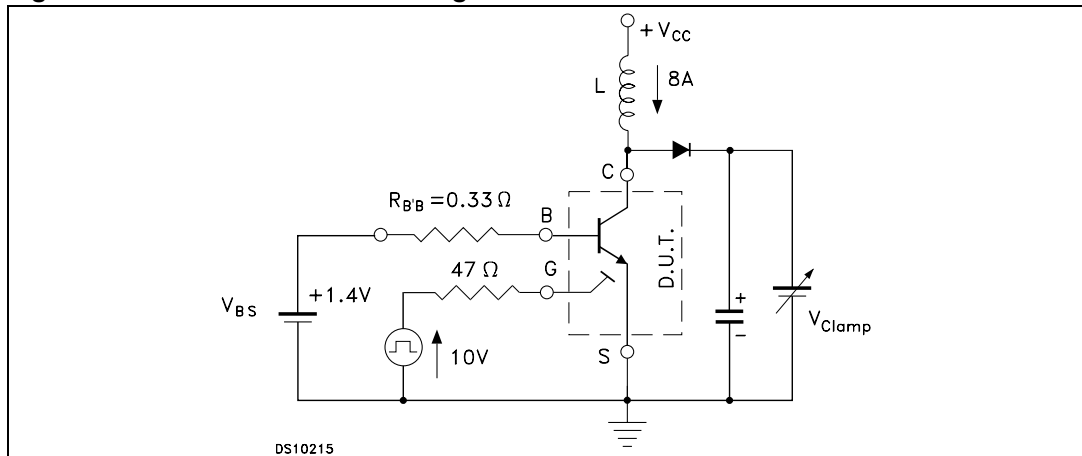


Figure 11. Inductive load switching time



2.2 Test circuits

Figure 12. Inductive load switching and RBSOA test circuit

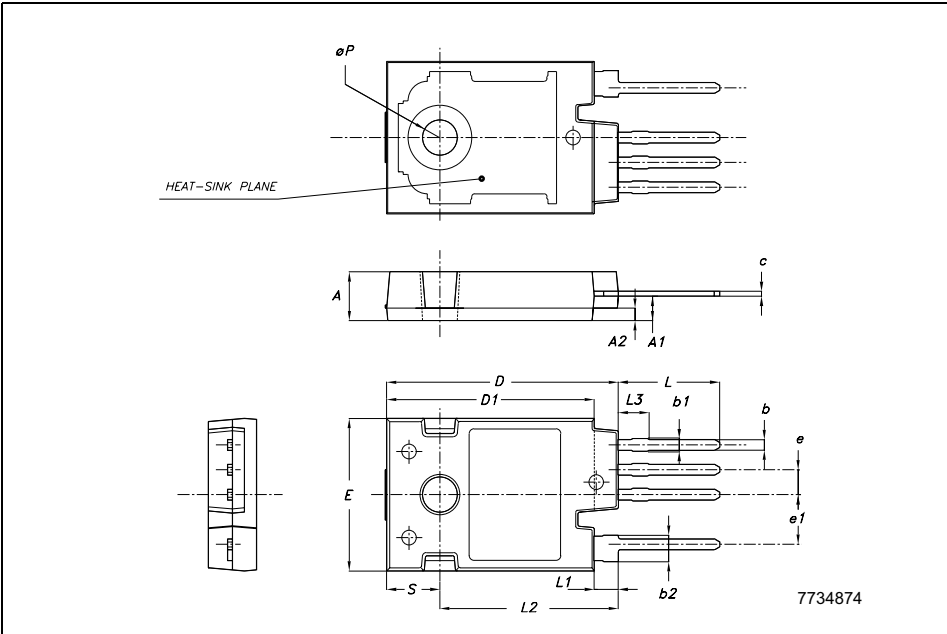


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO247-4LHV MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e	2.54		
e1	5.08		
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
∅P	3.55		3.65
S		5.50	



Revision history

Table 4. Revision history

Date	Revision	Changes
11-May-2006	1	Initial release.

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